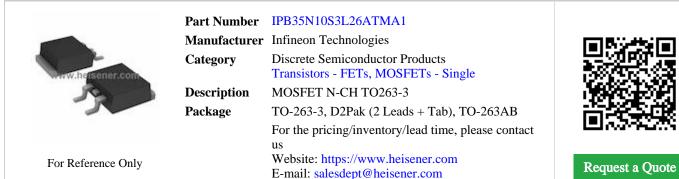


IPB35N10S3L26ATMA1

IPB35N10S3L26ATMA1 Information



Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.



IPB35N10S3L26ATMA1 Specifications

Manufacturer Part Number	IPB35N10S3L26ATMA1
Manufacturer	Infineon Technologies
Category	Discrete Semiconductor Products
	Transistors - FETs, MOSFETs - Single
Package	TO-263-3, D2Pak (2 Leads + Tab), TO-263AB
Series	Automotive, AEC-Q101, OptiMOS?
FET Type	N-Channel
Technology	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss)	100V
Current - Continuous Drain (Id) @ 25°C	35A (Tc)
Drive Voltage (Max Rds On, Min Rds On)	4.5V, 10V
Vgs(th) (Max) @ Id	2.4V @ 39µA
Gate Charge (Qg) (Max) @ Vgs	39nC @ 10V
Input Capacitance (Ciss) (Max) @ Vds	2700pF @ 25V
Vgs (Max)	$\pm 20\mathrm{V}$
FET Feature	-
Power Dissipation (Max)	71W (Tc)
Rds On (Max) @ Id, Vgs	26.3 mOhm @ 35A, 10V
Operating Temperature	-55°C ~ 175°C (TJ)
Mounting Type	Surface Mount
Supplier Device Package	PG-TO263-3-2
Package / Case	TO-263-3, D2Pak (2 Leads + Tab), TO-263AB
	Report errors

IPB35N10S3L26ATMA1 Guarantees



Quality Guarantees

We provide 90 days warranty. * If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction. Our experienced sales team and tech support team back our services to satisfy all our customers.

စ္ခ် MoneyGram <u>Alipay</u> VISA

DISCOVER

IPB35N10S3L26ATMA1 Payment Methods



IPB35N10S3L26ATMA1 Shipping Methods



If you have any question about IPB35N10S3L26ATMA1, please do not hesitate to contact us! Website: https://www.heisener.com E-mail: salesdept@heisener.com

UNION

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